

# NP45N06VDK

60 V – 45 A – N-channel Power MOS FET

R07DS1295EJ0100

Rev.1.00

Application: Automotive

Oct 26, 2015


## Description

NP45N06VDK is N-channel MOS Field Effect Transistor designed for high current switching applications.

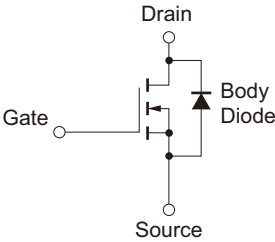
## Features

- Super low on-state resistance  
—  $R_{DS(on)1} = 11.6 \text{ m}\Omega \text{ MAX.}$  ( $V_{GS} = 10 \text{ V}, I_D = 23 \text{ A}$ )
- Low  $C_{iss}$ :  $C_{iss} = 1530 \text{ pF TYP.}$  ( $V_{DS} = 25 \text{ V}$ )
- Designed for automotive application and AEC-Q101 qualified

## Outline



TO-252(MP-3ZP)



Equivalent circuit

Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

## Ordering Information

Part No.	Lead Plating	Packing		Package
NP45N06VDK-E1-AY *1	Pure Sn (Tin)	Tape 2500 p/reel	Taping (E1 type)	TO-252(MP-3ZP)
NP45N06VDK-E2-AY *1			Taping (E2 type)	

Note: \*1. Pb-free (This product does not contain Pb in the external electrode)

**Absolute Maximum Ratings** ( $T_A = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to Source Voltage ( $V_{GS} = 0\text{ V}$ )	$V_{DSS}$	60	V
Gate to Source Voltage ( $V_{DS} = 0\text{ V}$ )	$V_{GSS}$	$\pm 20$	V
Drain Current (DC) ( $T_C = 25^\circ\text{C}$ )	$I_{D(DC)}$	$\pm 45$	A
Drain Current (pulse) <sup>*1</sup>	$I_{D(pulse)}$	$\pm 135$	A
Total Power Dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{T1}$	75	W
Total Power Dissipation ( $T_A = 25^\circ\text{C}$ )	$P_{T2}$	1.2	W
Channel Temperature	$T_{ch}$	175	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55 to +175	$^\circ\text{C}$
Repetitive Avalanche Current <sup>*2</sup>	$I_{AR}$	19	A
Repetitive Avalanche Energy <sup>*2</sup>	$E_{AR}$	36	mJ

Notes: \*1.  $T_C = 25^\circ\text{C}$ ,  $PW \leq 10\ \mu\text{s}$ , Duty Cycle  $\leq 1\%$

\*2.  $R_G = 25\ \Omega$ ,  $V_{GS} = 20\text{ V} \rightarrow 0\text{ V}$

**Thermal Resistance**

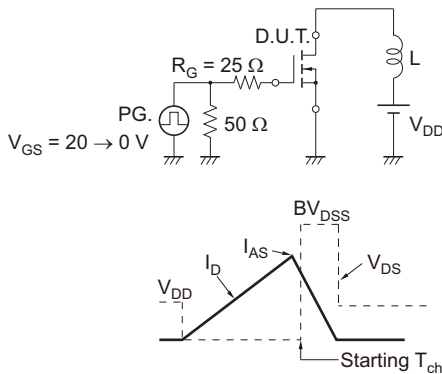
Channel to Case Thermal Resistance	$R_{th(ch-C)}$	2.00	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	125	$^\circ\text{C/W}$

**Electrical Characteristics** ( $T_A = 25^\circ\text{C}$ )

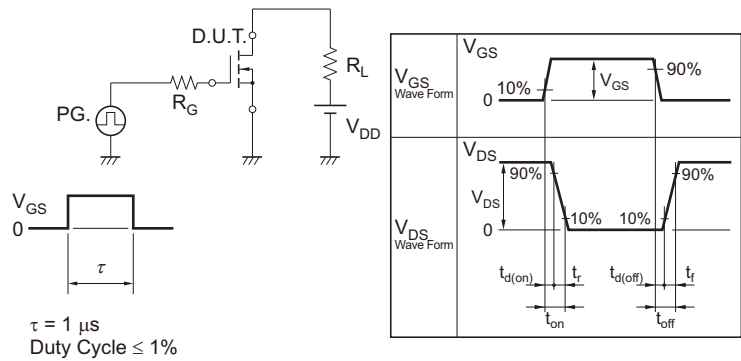
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	$I_{DSS}$			1	$\mu\text{A}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$
Gate Leakage Current	$I_{GSS}$			$\pm 100$	nA	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$
Gate to Source Threshold Voltage	$V_{GS(th)}$	1.5	2.1	2.5	V	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$
Forward Transfer Admittance *1	$ y_{fs} $	15	39		S	$V_{DS} = 5\text{ V}, I_D = 23\text{ A}$
Drain to Source On-state Resistance *1	$R_{DS(on)1}$		9.0	11.6	m $\Omega$	$V_{GS} = 10\text{ V}, I_D = 23\text{ A}$
	$R_{DS(on)2}$		11.5	19.6	m $\Omega$	$V_{GS} = 4.5\text{ V}, I_D = 23\text{ A}$
Input Capacitance	$C_{iss}$		1530	2300	pF	$V_{DS} = 25\text{ V},$ $V_{GS} = 0\text{ V},$ $f = 1\text{ MHz}$
Output Capacitance	$C_{oss}$		155	240	pF	
Reverse Transfer Capacitance	$C_{rss}$		55	100	pF	
Turn-on Delay Time	$t_{d(on)}$		15	40	ns	$V_{DD} = 30\text{ V}, I_D = 23\text{ A},$ $V_{GS} = 10\text{ V},$ $R_G = 0\ \Omega$
Rise Time	$t_r$		5	20	ns	
Turn-off Delay Time	$t_{d(off)}$		37	80	ns	
Fall Time	$t_f$		3	10	ns	
Total Gate Charge	$Q_G$		25	38	nC	$V_{DD} = 48\text{ V},$ $V_{GS} = 10\text{ V},$ $I_D = 45\text{ A}$
Gate to Source Charge	$Q_{GS}$		6		nC	
Gate to Drain Charge	$Q_{GD}$		6		nC	
Body Diode Forward Voltage *1	$V_{F(S-D)}$		0.9	1.5	V	$I_F = 45\text{ A}, V_{GS} = 0\text{ V}$
Reverse Recovery Time	$t_{rr}$		28		ns	$I_F = 45\text{ A}, V_{GS} = 0\text{ V},$ $di/dt = 100\text{ A}/\mu\text{s}$
Reverse Recovery Charge	$Q_{rr}$		20		nC	

Note: \*1. Pulsed test

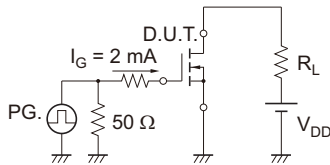
**TEST CIRCUIT 1 AVALANCHE CAPABILITY**



**TEST CIRCUIT 2 SWITCHING TIME**

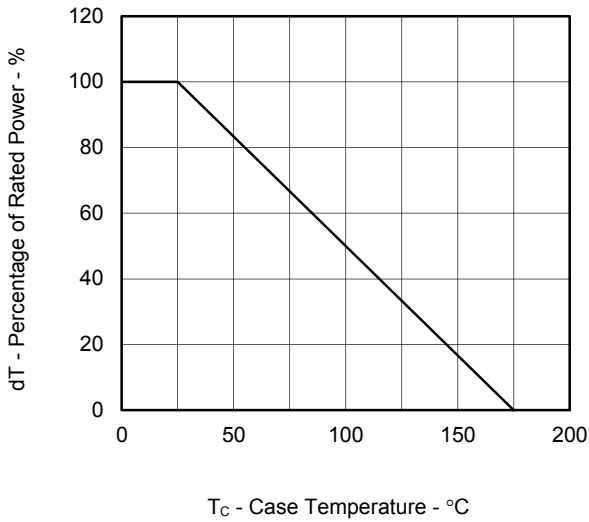


**TEST CIRCUIT 3 GATE CHARGE**

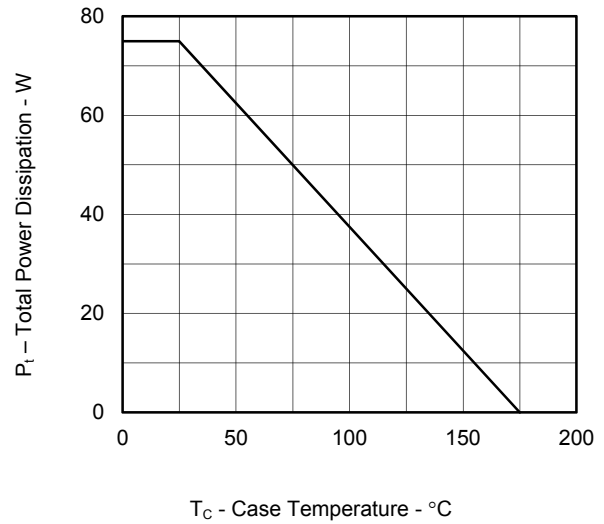


**Typical Characteristics (T<sub>A</sub> = 25°C)**

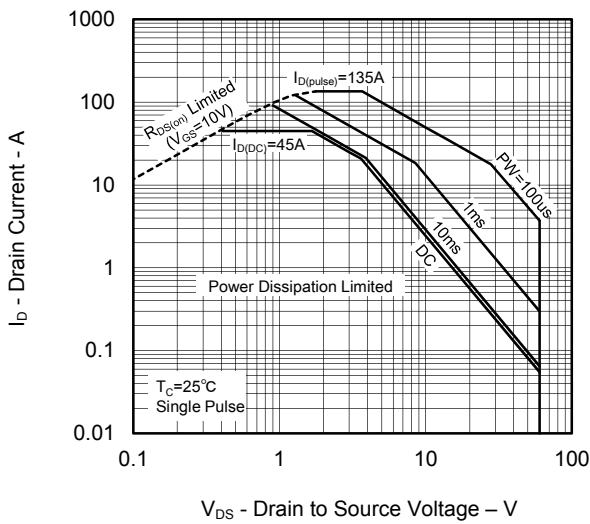
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



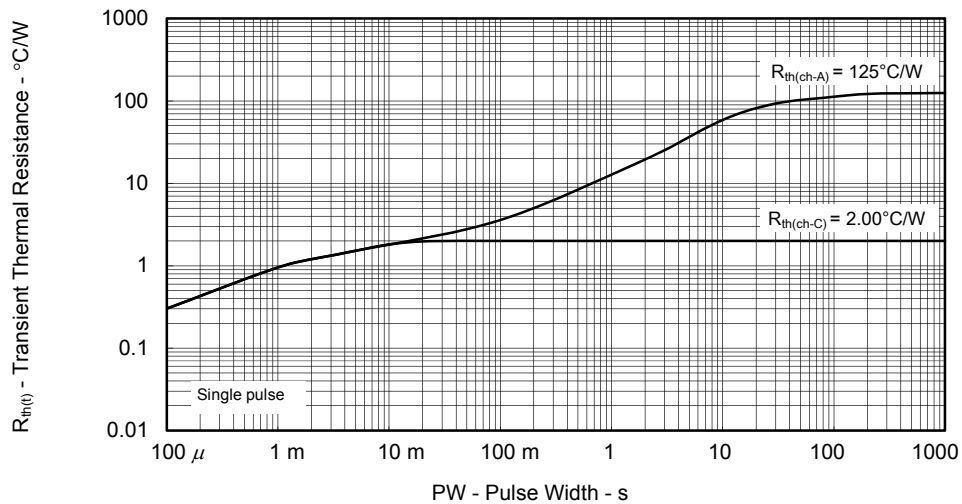
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE



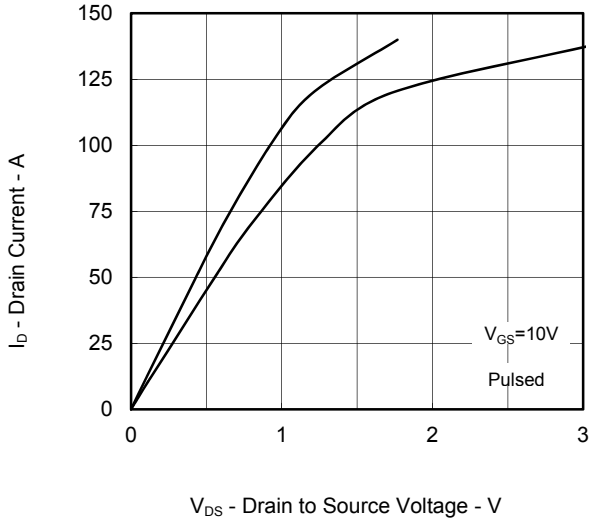
FORWARD BIAS SAFE OPERATING AREA



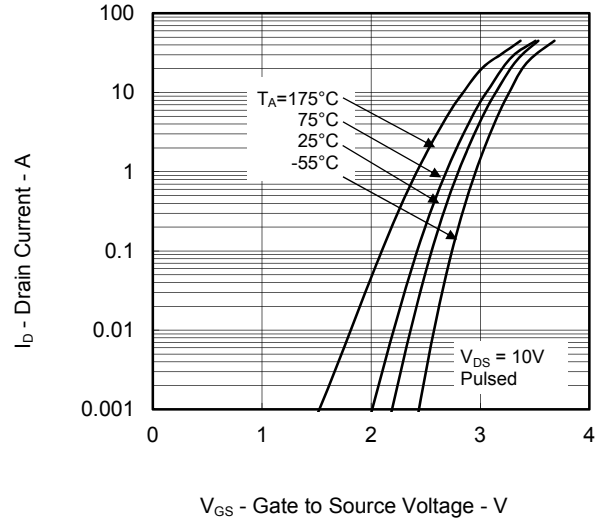
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



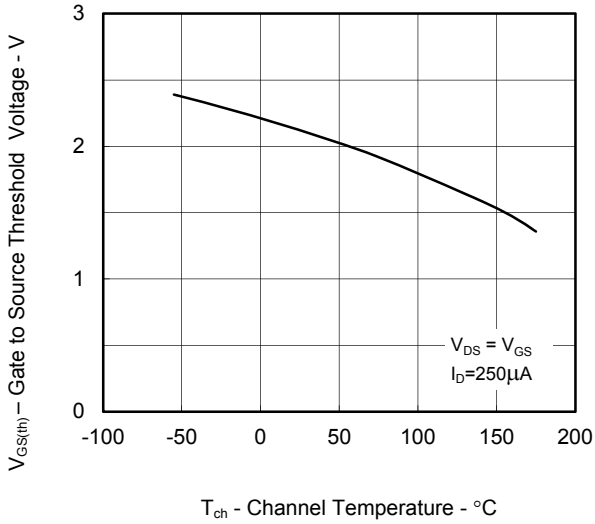
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



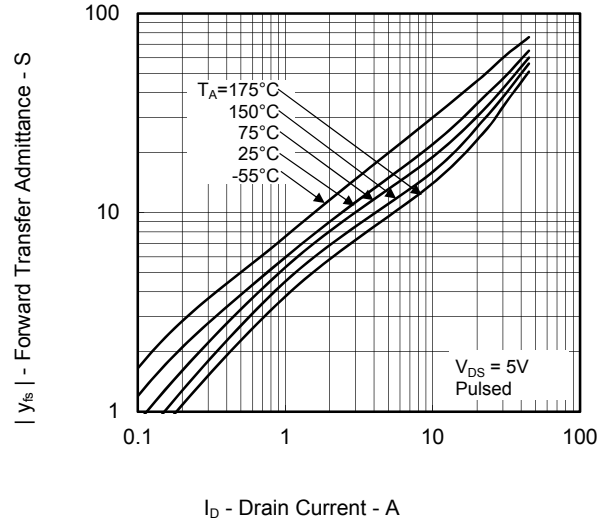
FORWARD TRANSFER CHARACTERISTICS



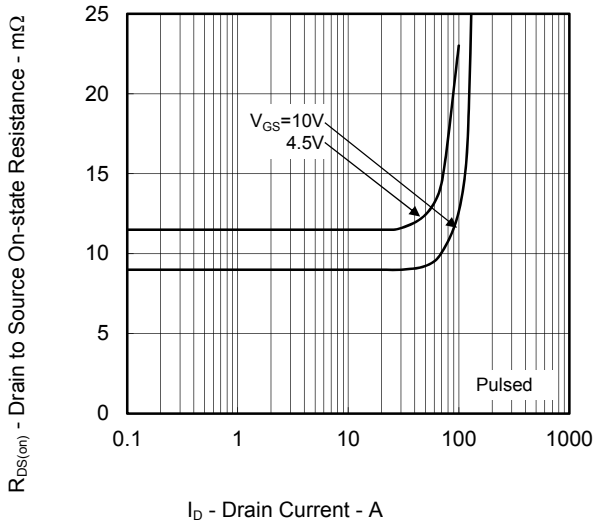
GATE TO SOURCE THRESHOLD VOLTAGE vs. CHANNEL TEMPERATURE



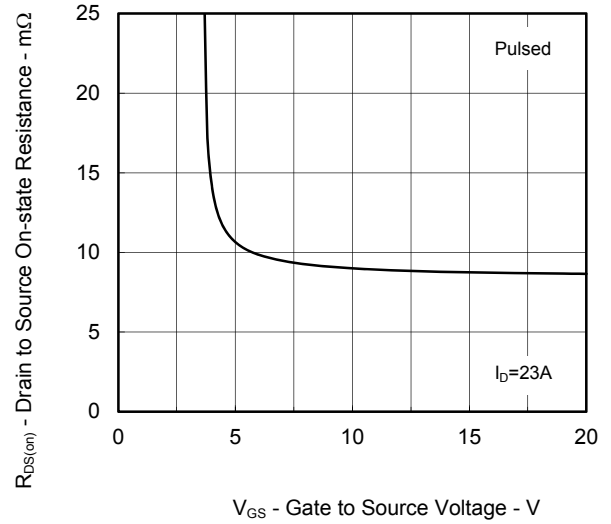
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



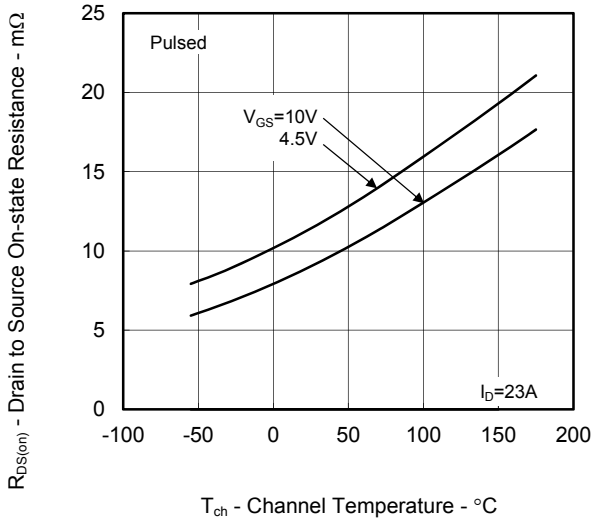
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



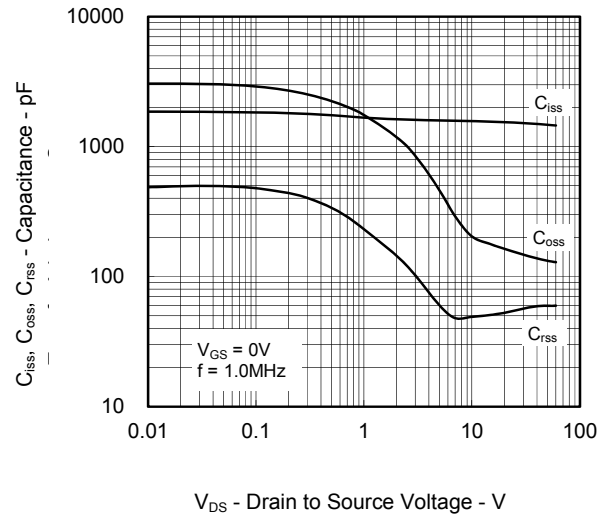
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



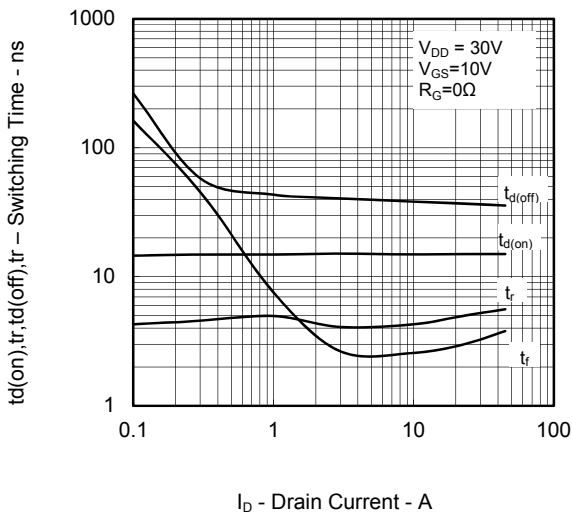
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



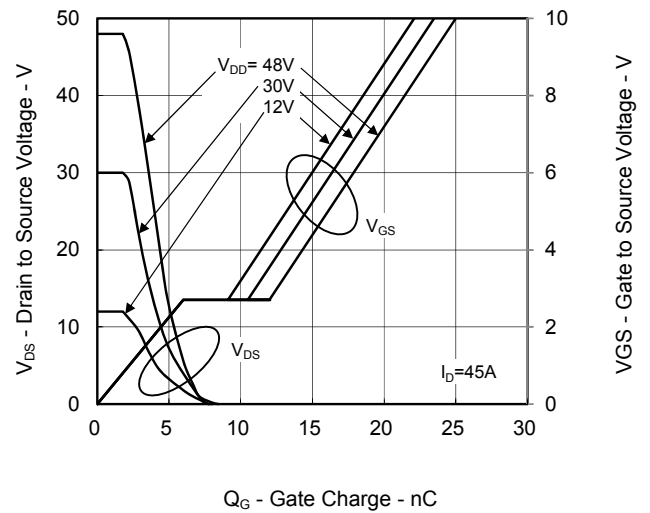
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



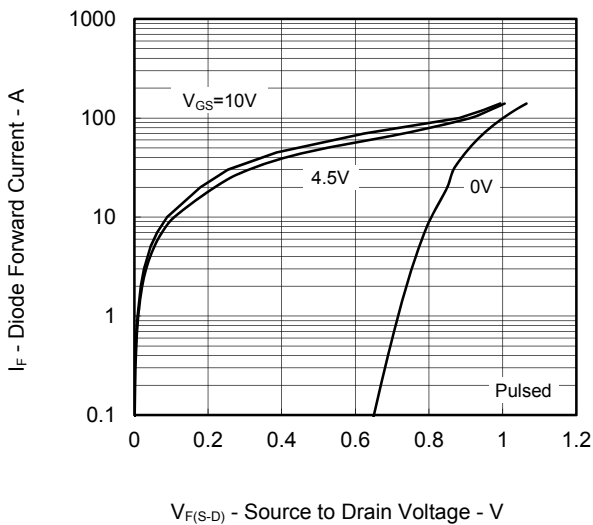
SWITCHING CHARACTERISTICS



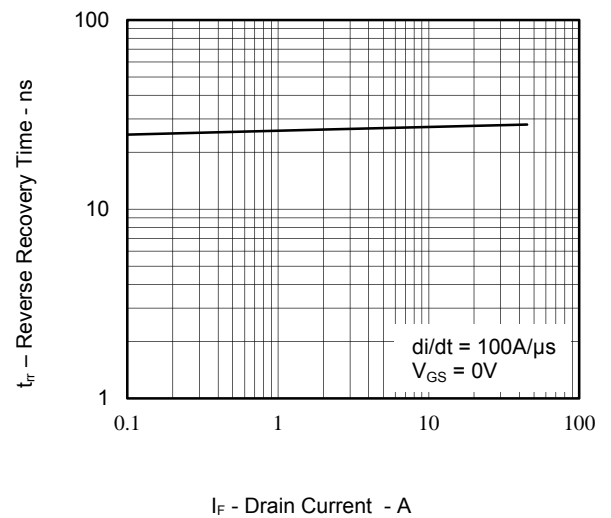
DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



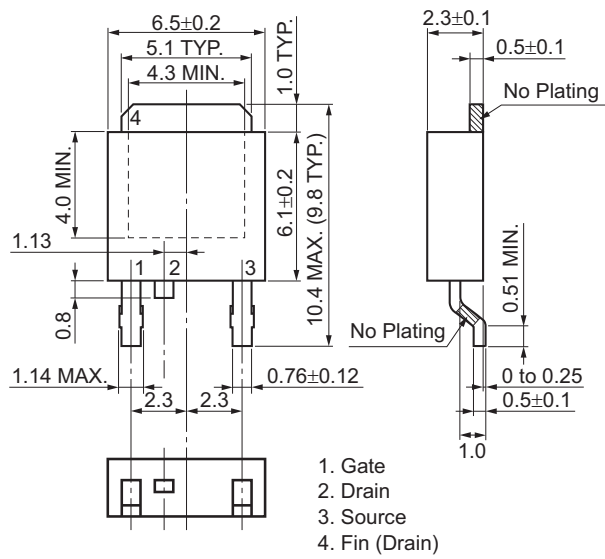
REVERSE RECOVERY TIME vs. DRAIN CURRENT



**Package Drawings (Unit: mm)**

**TO-252 (MP-3ZP) (Mass: 0.3 g TYP.)**

Renesas package code: PRSS0004ZP-A



<b>Revision History</b>	<b>NP45N06VDK Data Sheet</b>
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Rev.	Date	Description	
		Page	Summary
1.00	Oct. 26, 2015	—	First Edition Issued

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